

$V_{DSS}$	650V
$R_{DS(on)}$ (Typ.)	120mΩ
$I_D$	29A
$P_D$	165W

#### ●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

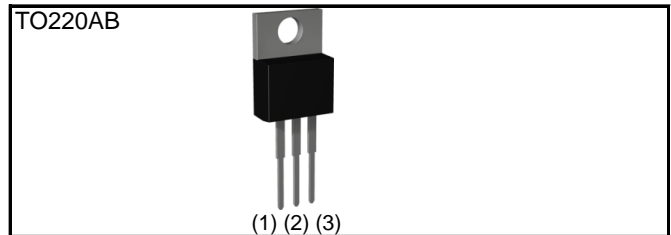
#### ●Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

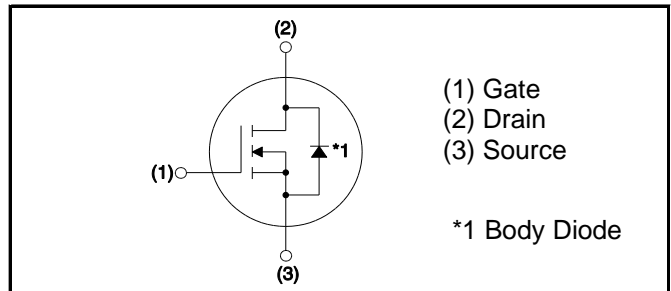
#### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{DSS}$	650	V	
Continuous drain current	$T_c = 25^\circ\text{C}$	$I_D^{*1}$	29	A
	$T_c = 100^\circ\text{C}$	$I_D^{*1}$	20	A
Pulsed drain current	$I_{D,pulse}^{*2}$	72	A	
Gate - Source voltage	$V_{GSS}$	-6 to 22	V	
Power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	165	W	
Junction temperature	$T_j$	175	$^\circ\text{C}$	
Range of storage temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$	

#### ●Outline



#### ●Inner circuit



#### ●Packaging specifications

Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	50
	Taping code	-
	Marking	SCT2120AF

### ●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	$R_{thJC}$	-	0.70	0.91	°C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	°C

### ●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	650	-	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V$ $T_j = 25^\circ\text{C}$	-	1	10	$\mu\text{A}$
		$T_j = 150^\circ\text{C}$	-	2	-	
Gate - Source leakage current	$I_{GSS+}$	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	$I_{GSS-}$	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 3.3mA$	1.6	-	4.0	V
Static drain - source on - state resistance	$R_{DS(on)}^{*3}$	$V_{GS} = 18V, I_D = 10A$ $T_j = 25^\circ\text{C}$	-	120	156	$m\Omega$
		$T_j = 125^\circ\text{C}$	-	149	-	
Gate input resistance	$R_G$	$f = 1MHz, \text{open drain}$	-	13.8	-	$\Omega$

**●Electrical characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	$g_{fs}^{*3}$	V <sub>DS</sub> = 10V, I <sub>D</sub> = 10A	-	2.7	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	1200	-	pF
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 500V	-	90	-	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	13	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V V <sub>DS</sub> = 0V to 300V	-	115	-	pF
Turn - on delay time	t <sub>d(on)</sub> <sup>*3</sup>	V <sub>DD</sub> = 300V, I <sub>D</sub> = 10A	-	22	-	ns
Rise time	t <sub>r</sub> <sup>*3</sup>	V <sub>GS</sub> = 18V/0V	-	31	-	
Turn - off delay time	t <sub>d(off)</sub> <sup>*3</sup>	R <sub>L</sub> = 30Ω	-	60	-	
Fall time	t <sub>f</sub> <sup>*3</sup>	R <sub>G</sub> = 0Ω	-	19	-	
Turn - on switching loss	E <sub>on</sub> <sup>*3</sup>	V <sub>DD</sub> = 300V, I <sub>D</sub> = 10A V <sub>GS</sub> = 18V/0V	-	61	-	μJ
Turn - off switching loss	E <sub>off</sub> <sup>*3</sup>	R <sub>G</sub> = 0Ω, L = 500μH *E <sub>on</sub> includes diode reverse recovery	-	41	-	

**●Gate Charge characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q <sub>g</sub> <sup>*3</sup>	V <sub>DD</sub> = 300V	-	61	-	nC
Gate - Source charge	Q <sub>gs</sub> <sup>*3</sup>	I <sub>D</sub> = 10A	-	14	-	
Gate - Drain charge	Q <sub>gd</sub> <sup>*3</sup>	V <sub>GS</sub> = 18V	-	21	-	
Gate plateau voltage	V <sub>(plateau)</sub>	V <sub>DD</sub> = 300V, I <sub>D</sub> = 10A	-	10.4	-	V

\*1 Limited only by maximum temperature allowed.

\*2 PW ≤ 10μs, Duty cycle ≤ 1%

\*3 Pulsed

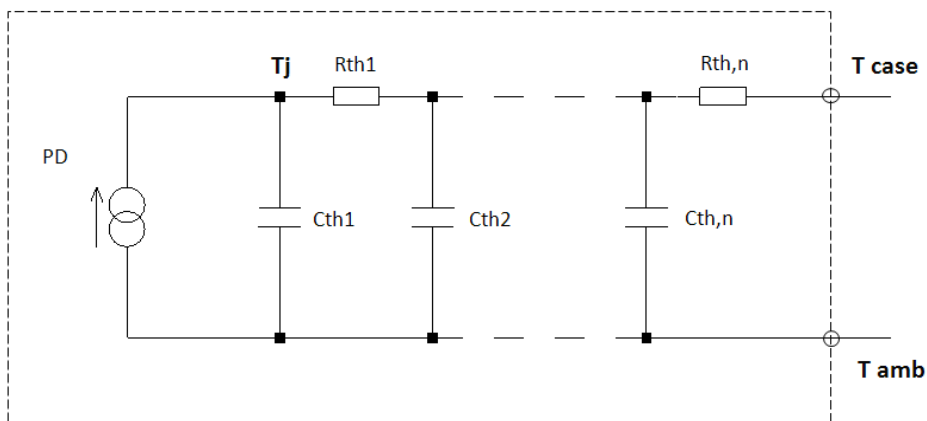
●Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	$I_S^{*1}$	$T_C = 25^\circ\text{C}$	-	-	29	A
Inverse diode direct current, pulsed	$I_{SM}^{*2}$		-	-	72	A
Forward voltage	$V_{SD}^{*3}$	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	4.3	-	V
Reverse recovery time	$t_{rr}^{*3}$	$I_F = 10\text{A}, V_R = 400\text{V}$ $di/dt = 160\text{A}/\mu\text{s}$	-	33	-	ns
Reverse recovery charge	$Q_{rr}^{*3}$		-	53	-	nC
Peak reverse recovery current	$I_{rrm}^{*3}$		-	3.0	-	A

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
$R_{th1}$	96.1m	K/W
$R_{th2}$	404m	
$R_{th3}$	196m	

Symbol	Value	Unit
$C_{th1}$	1.55m	Ws/K
$C_{th2}$	5.23m	
$C_{th3}$	83.3m	



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

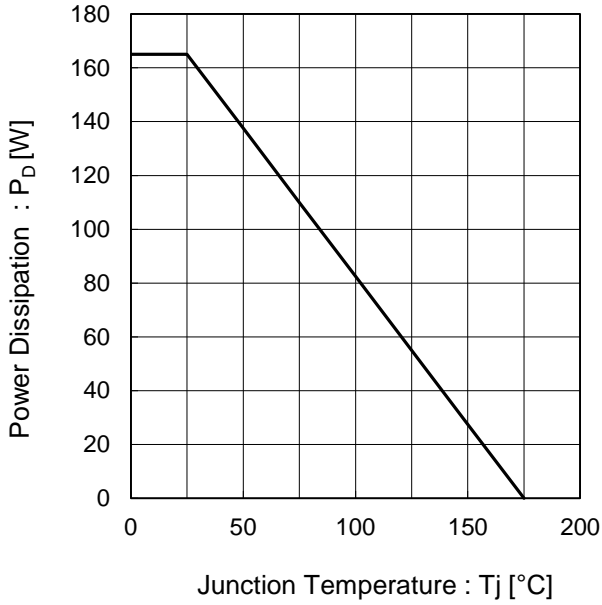


Fig.2 Maximum Safe Operating Area

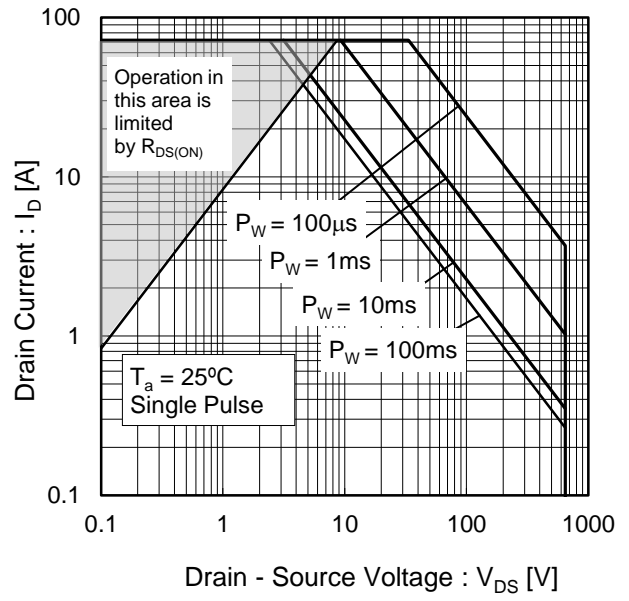
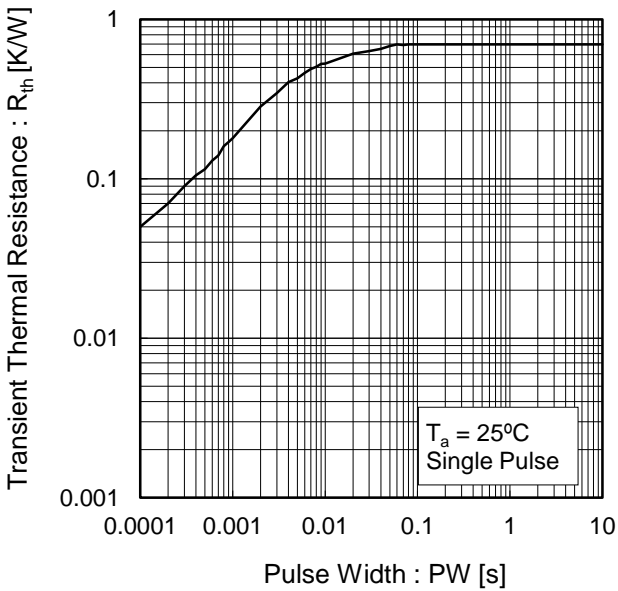


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

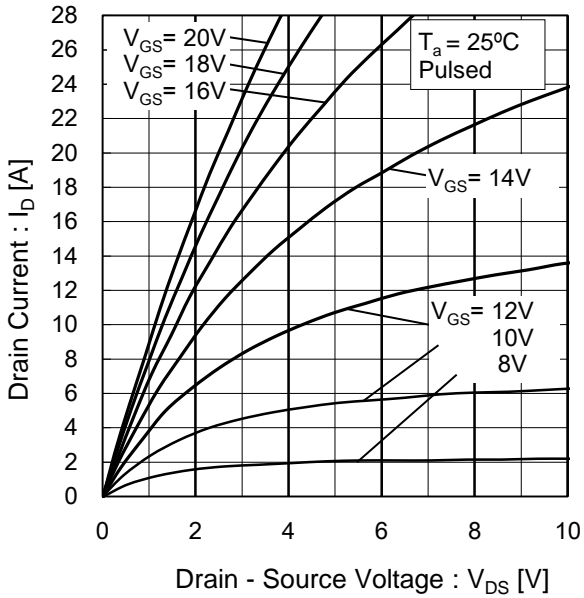


Fig.5 Typical Output Characteristics(II)

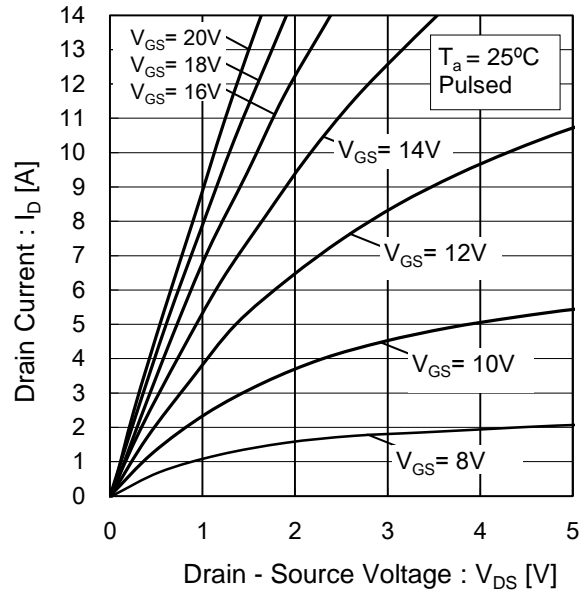


Fig.6  $T_j = 150^\circ\text{C}$  Typical Output Characteristics(I)

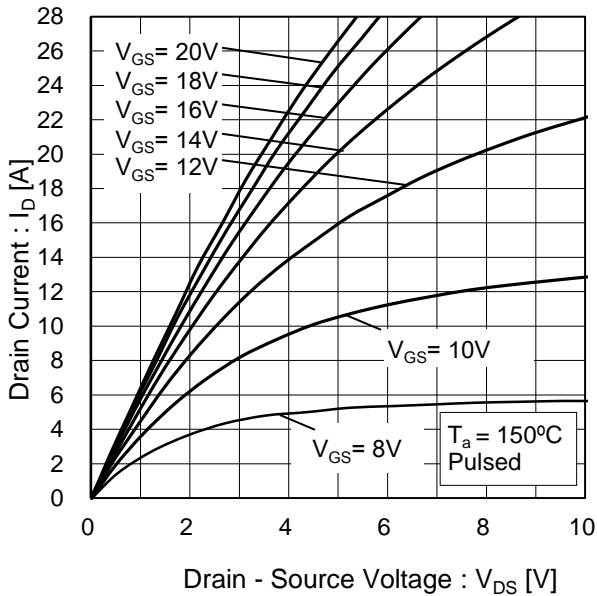
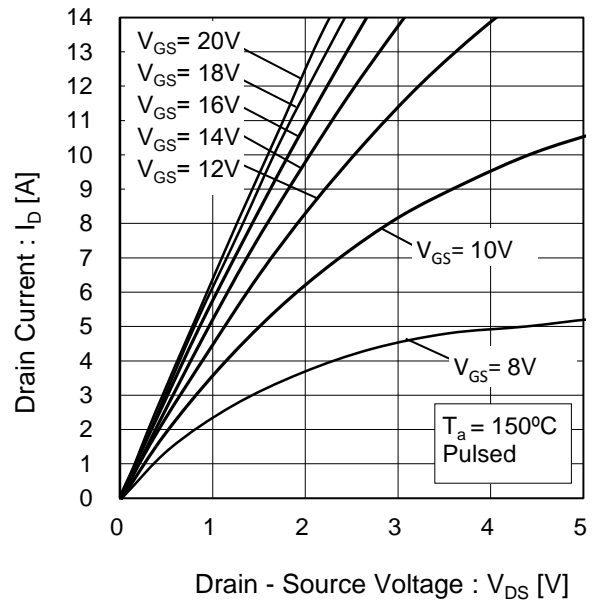


Fig.7  $T_j = 150^\circ\text{C}$  Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)

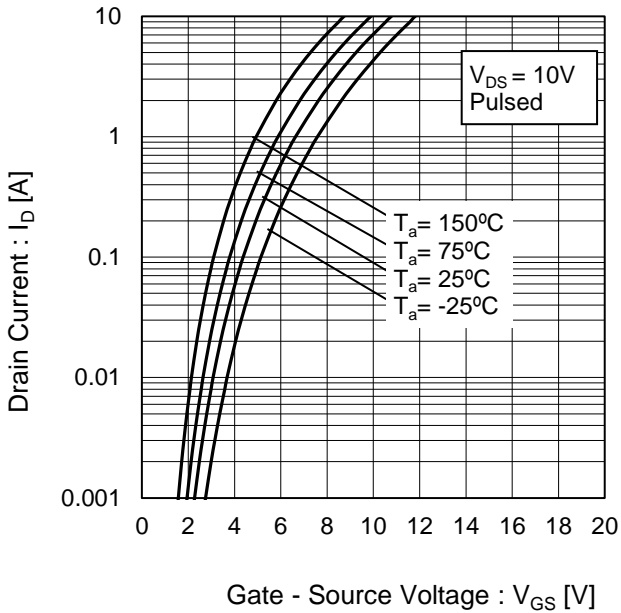


Fig.9 Typical Transfer Characteristics (II)

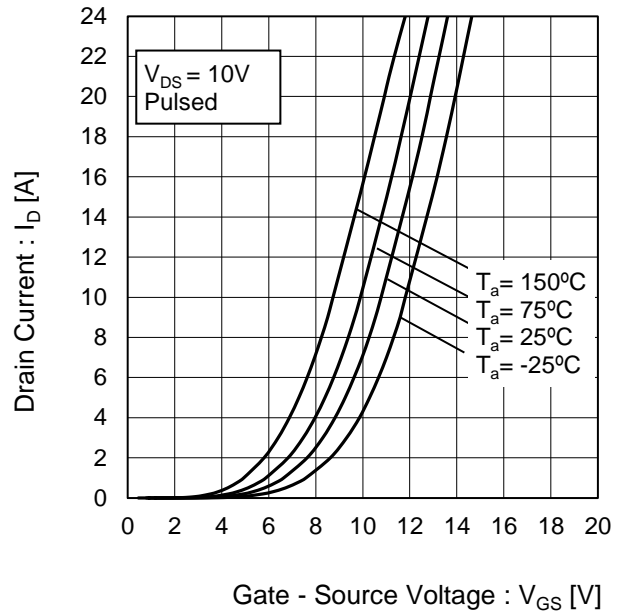


Fig.10 Gate Threshold Voltage vs. Junction Temperature

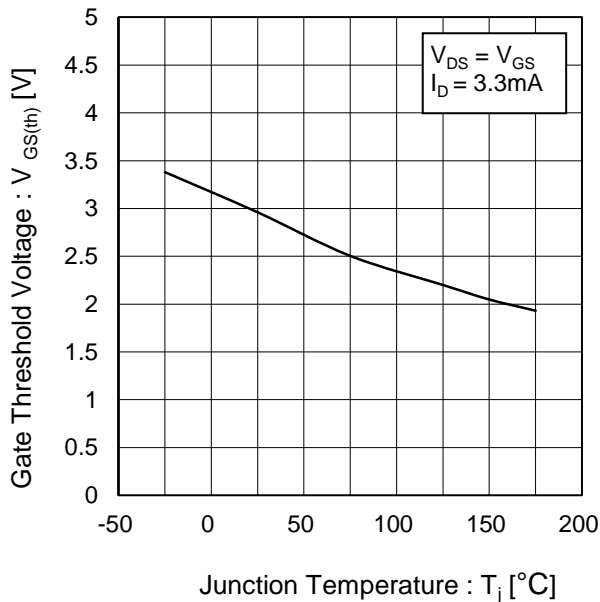
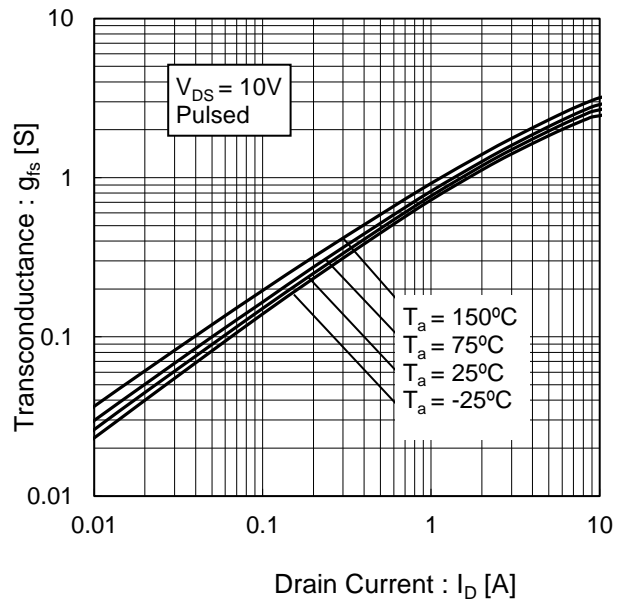


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

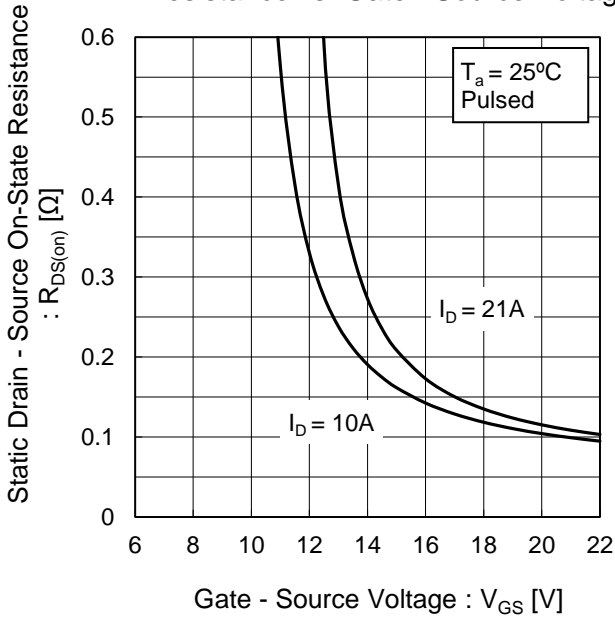


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

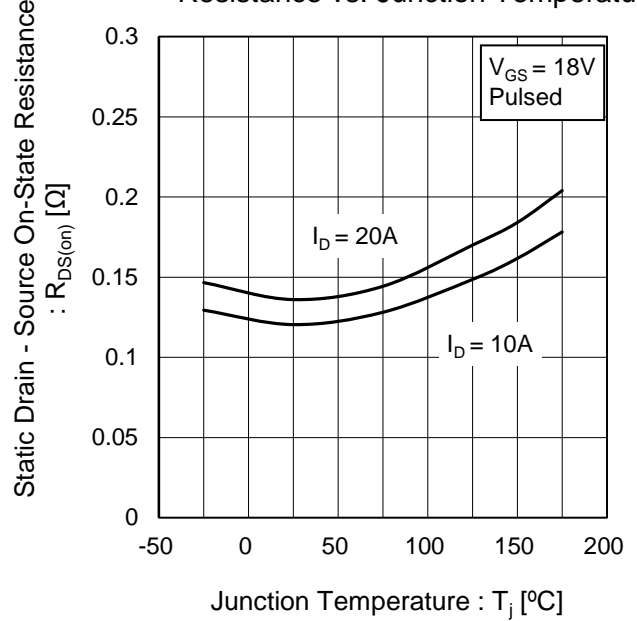
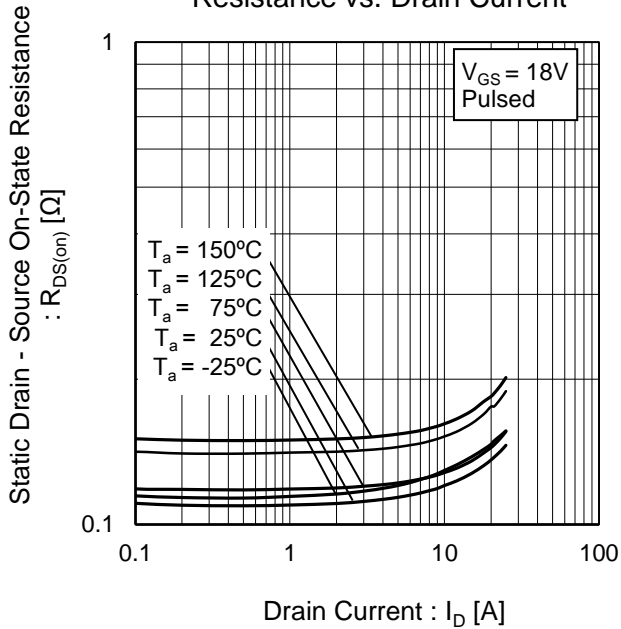


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current





●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

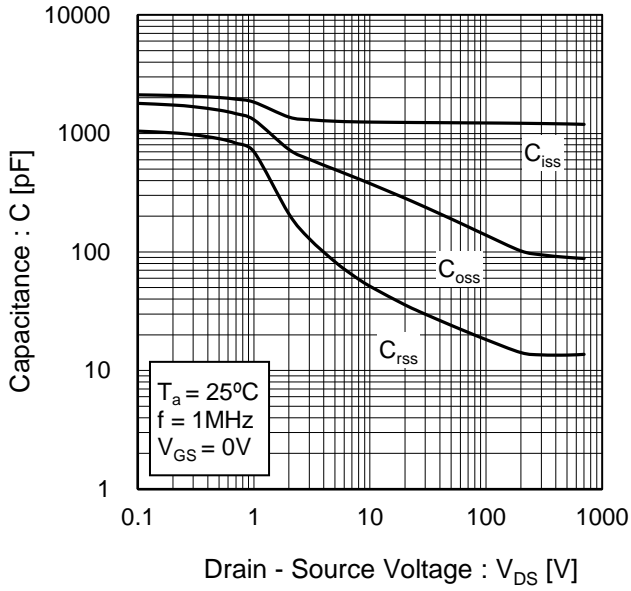


Fig.16 Coss Stored Energy

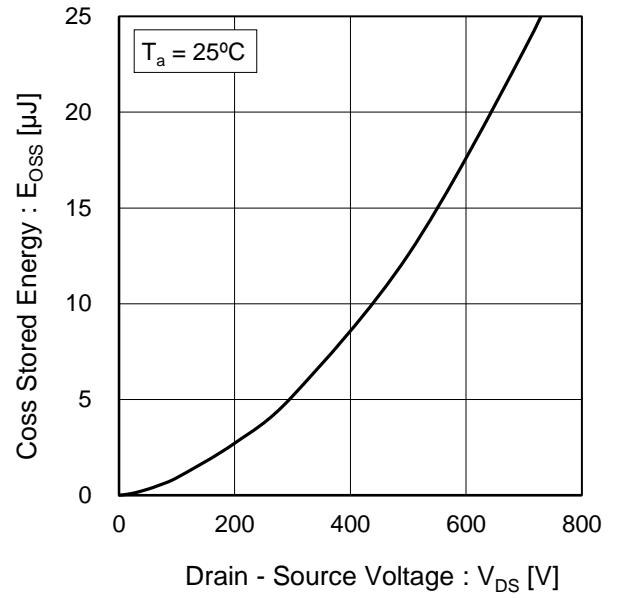


Fig.17 Switching Characteristics

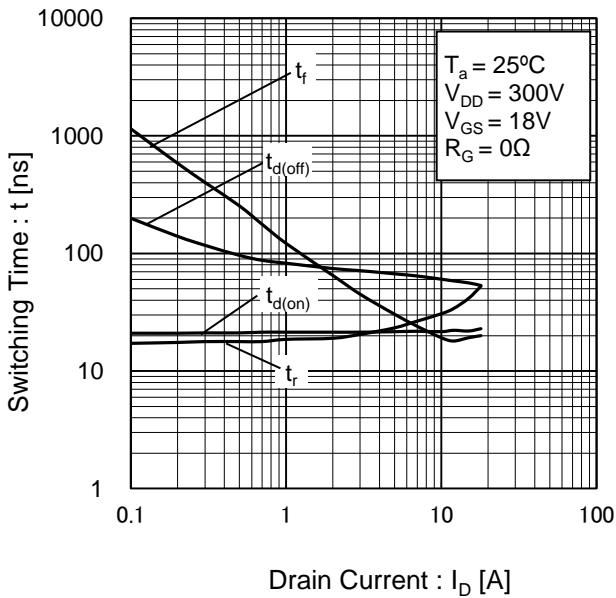
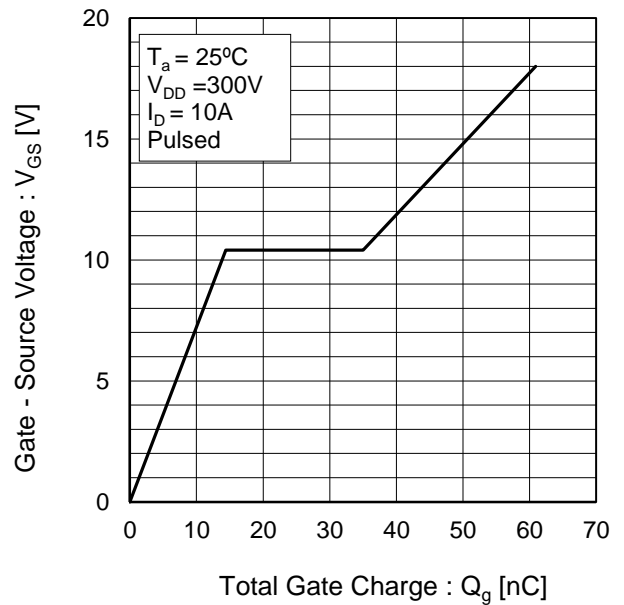


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

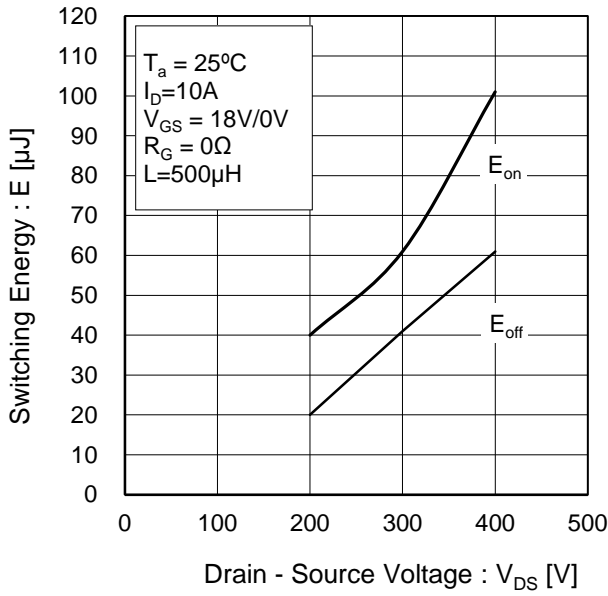


Fig.20 Typical Switching Loss vs. Drain Current

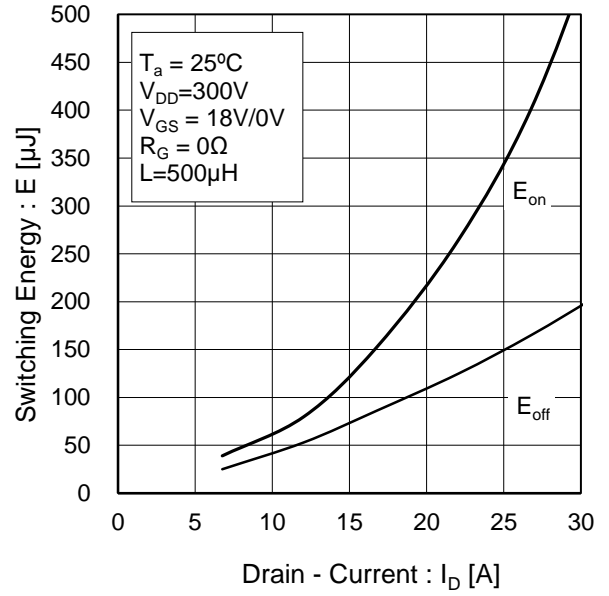
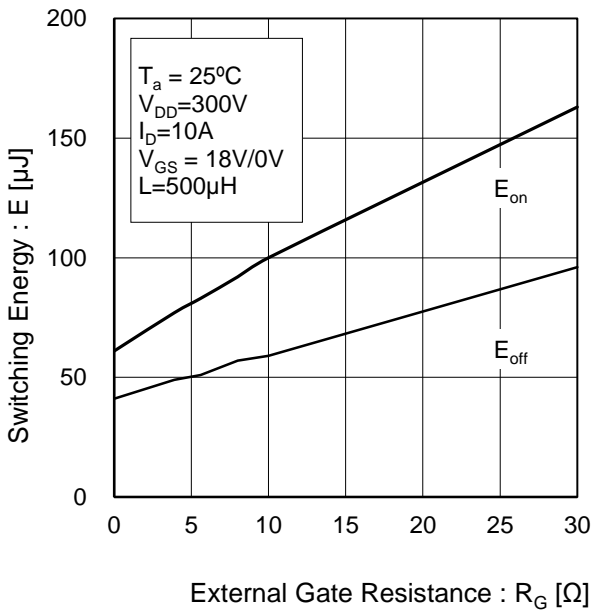


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

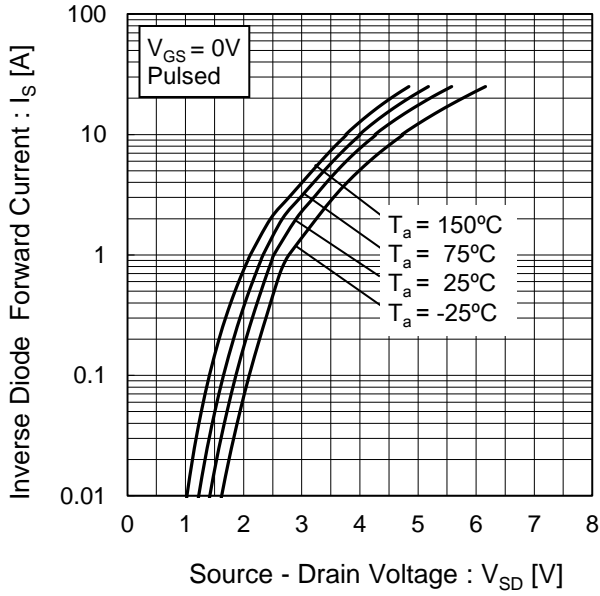
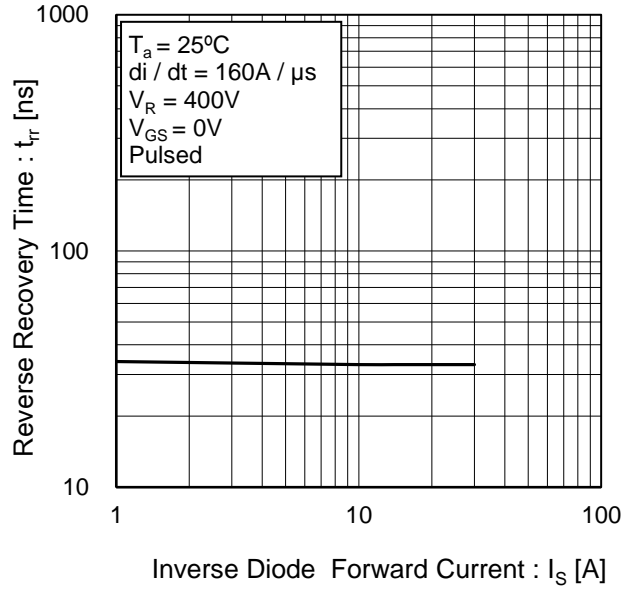


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

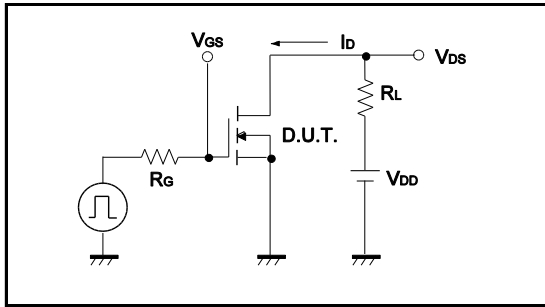


Fig.1-2 Switching Waveforms

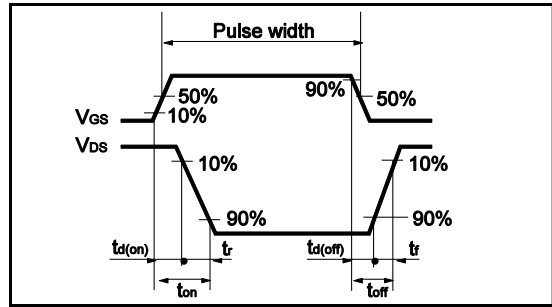


Fig.2-1 Gate Charge Measurement Circuit

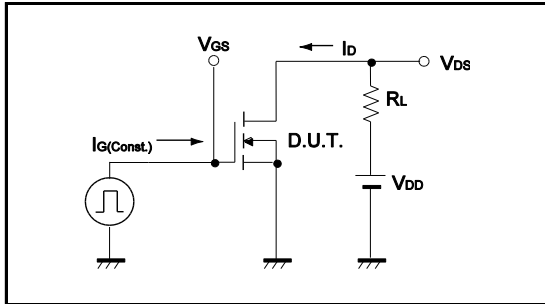


Fig.2-2 Gate Charge Waveform

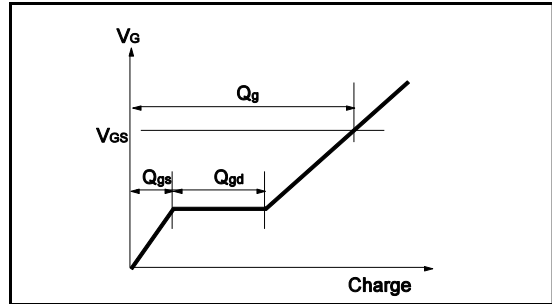


Fig.3-1 Switching Energy Measurement Circuit

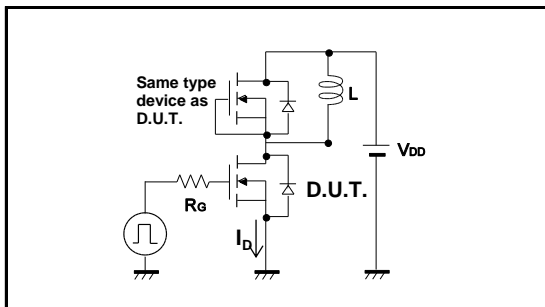


Fig.3-2 Switching Waveforms

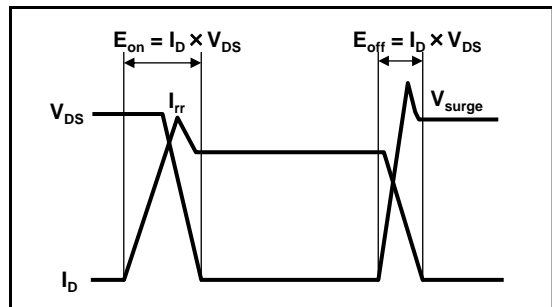


Fig.4-1 Reverse Recovery Time Measurement Circuit

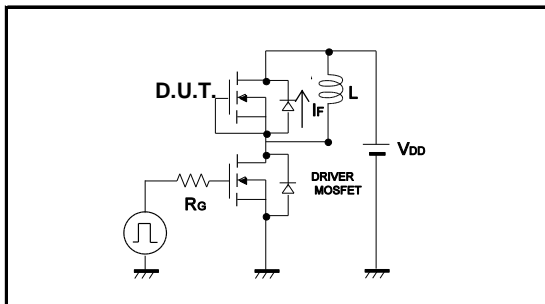
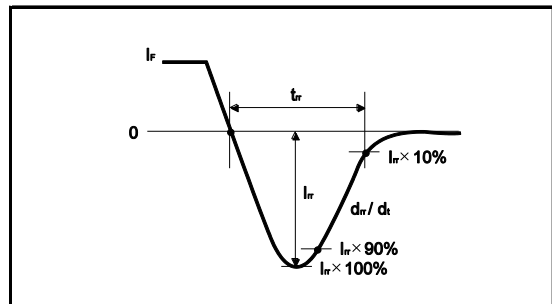
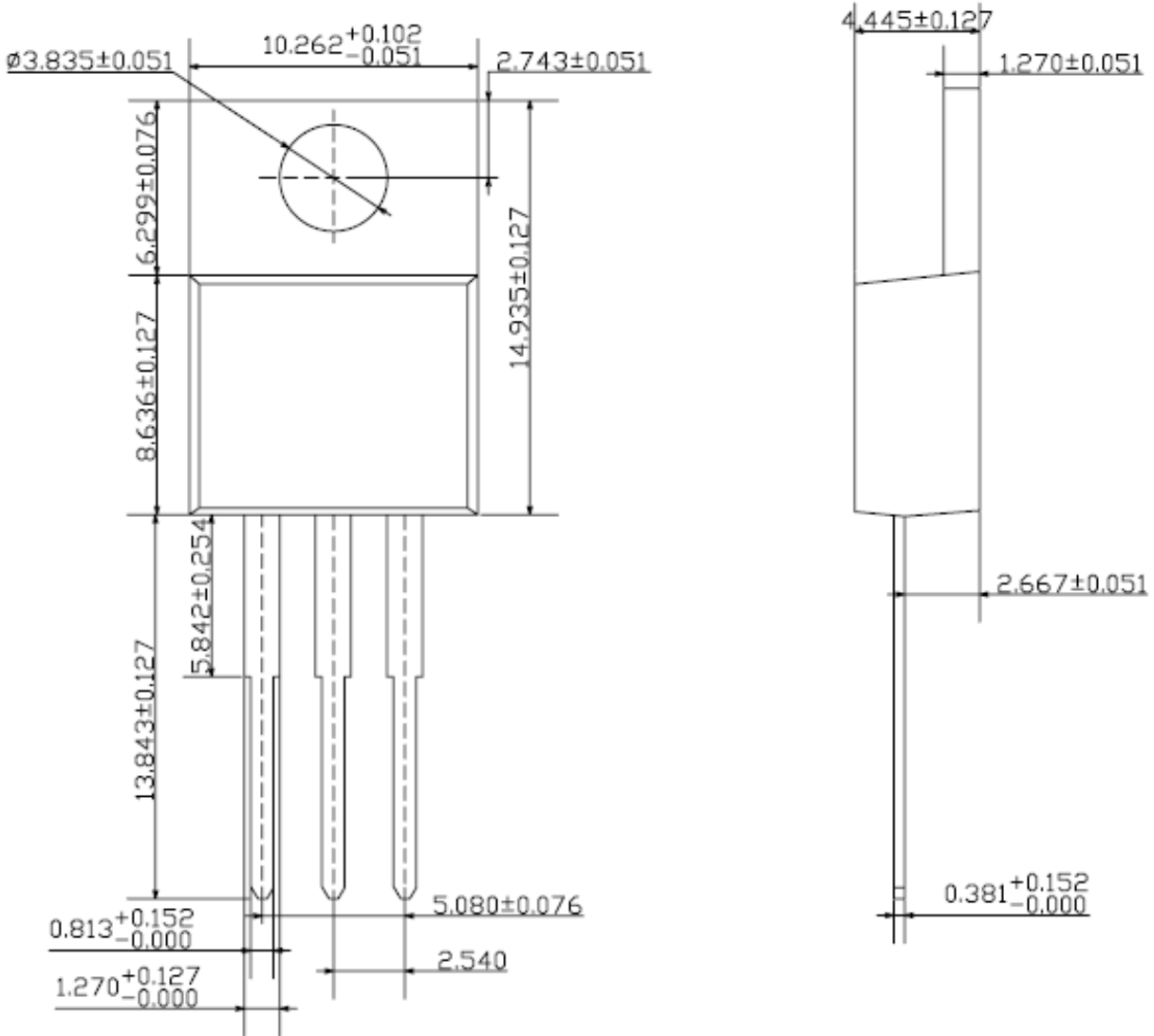


Fig.4-2 Reverse Recovery Waveform



●Dimensions (Unit : mm)

TO-220AB



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